

CLAIMS

1. A two-dimensional patterning method, wherein a two-dimensional pattern is formed by destroying a blister disposed on a substrate by electron irradiation.

2. A two-dimensional patterning method, wherein a two-dimensional pattern is formed by destroying a blister disposed on a substrate by ion irradiation.

3. A two-dimensional patterning method, wherein a two-dimensional pattern of a uncoated clean surface is formed by forming a film on a blister disposed on a substrate and destroying and removing the blister together with the formed film by electron irradiation or ion irradiation.

4. A two-dimensional patterning method, wherein a two-dimensional pattern of a non-reacted clean surface is formed by executing surface reaction on a blister disposed on a substrate and destroying and removing the blister together with the reacted film by electron irradiation or ion irradiation.

5. A two-dimensional patterning method, wherein a two-dimensional pattern is formed by forming a film on a blister disposed on a substrate and destroying and removing the blister together with the formed film by electron irradiation or ion irradiation, and further by forming a film on the surface from which the blister has been destroyed and removed with the use of difference in adsorption probability between the substrate surface protected by the blister and the surface not protected.

6. A two-dimensional patterning method, wherein a two-dimensional pattern is formed by executing surface reaction on a blister disposed on a substrate and destroying and removing the blister together with the reacted film by electron irradiation or ion irradiation, and further by executing chemical reaction on the surface from which the blister has been destroyed and removed with the use of difference in reactivity between the substrate surface protected by the blister and the surface not protected.

7. The two-dimensional patterning method according to any one of claims 1 to 6, wherein the substrate is a silicon substrate or a metal substrate.

8. The two-dimensional patterning method according to any one of claims 1 to 6, wherein the blister is formed by hydrogen ion irradiation, deuterium ion irradiation, or helium ion irradiation.

9. The two-dimensional patterning method according to any one of claims 1 to 6, wherein the blister having a patterned configuration is formed by ion irradiation through a mask.

10. The two-dimensional patterning method according to any one of claims 1 to 6, wherein the blister having a patterned configuration is formed by using focused ion beam.

11. The two-dimensional patterning method according to claim 2, wherein the irradiation ion is any one of Ar^+ , Kr^+ , and Xe^+ .

12. The two-dimensional patterning method according to any one of claims 1 to 6, wherein the two-dimensional pattern is a pattern of an atomic species of a surface constituent atom.

13. The two-dimensional patterning method according to any one of claims 1 to 6, wherein the two-dimensional pattern is a pattern different in film formed in a lower layer than a surface layer.

14. The two-dimensional patterning method according to any one of claims 1 to 6, wherein the two-dimensional pattern is an electric characteristic pattern.

15. The two-dimensional patterning method according to any one of claims 1 to 6, wherein the two-dimensional pattern is a reactive pattern.

16. The two-dimensional patterning method according to claim 15, wherein the two-dimensional pattern is an affinity pattern.

17. The two-dimensional patterning method according to claim 16, wherein the two-dimensional pattern is a hydrophilic or hydrophobic pattern.

18. A manufacturing method of electronic device, wherein the two-dimensional patterning method according to any one of claims 1 to 17 is employed.

19. A manufacturing method of magnetic device, wherein the two-dimensional

patterning method according to any one of claims 1 to 17 is employed.